MICRO ELECTRONICS

2SA673

SILICON
TRANSISTOR

2SA673 is PNP silicon epitaxial transistor design for medium power amplifiers and switching applications.

ECB

ABSOLUTE MAXIMUM RATINGS

Collector-Base Voltage	VCBO	35V
Collector-Emitter Voltage	VCEO	35V
Emitter-Base Voltage	VEBO	4V
Collector Current	IC	500mA
Total Power Dissipation	Ptot	400mW
Operating Junction & Storage Temperature	Tj,Tstg	-55 to +150°C

ELECTRICAL CHARACTERISTICS (TA=25°C)

PARAMETER	SYMBOL	MIN	MAX	UNIT	TEST CONDITIONS
Collector Cutoff Current	ICBO		500	nA	VCB=20V IE=0
D.C. Current Gain	HFE	60	320		IC=10mA VCE=3V
Collector-Emitter Saturation Voltage	VCE(sat)		0.4	V	IC=100mA IB=10mA*
Base-Emitter Saturation Voltage	VBE(sat)		1	V	IC=100mA IB=10mA*
Collector-Base Breakdown Voltage	BVCBO	35		V	IC=100μA IE=0
Collector-Emitter Breakdown Voltage	LVCEO	35		V	IC=10mA IB=0
Emitter-Base Breakdown Voltage	BVEBO	4		V	IE=100μA IC=0
Current Gain-Bandwidth Product	fT	120 TYP.		MHz	IC=10mA VCE=10V
Output Capacitance	Cob	7TYP.		pF	VCB=10V f=1MHz

MICRO ELECTRONICS LTD. 美科有限公司

38, Hung To Road, Microtron Building, Kwun Tong, Kowloon, Hong Kong.
Kwun Tong P.O. Box 69477 Hong Kong. Fax No. 341 0321 Telex: 43510 Micro Hx. Tel: 343 0181-5

* Pulse test.

1-1.BMP